In the claims:

Claims 1-13 (Canceled)

14. (Currently amended) A method of forming a dielectric substrate having a multiturn inductor, the method comprising the steps of:

a) obtaining a plurality of layers;

b) forming conductive lines on a first group of layers;

c) forming conductive vias in a second group of layers;

d) forming conductive lines on a third group of layers;

e) stacking at least one layer from the second group of layers on at least ~~one layer~~ two layers from the third group of layers; and

f) stacking at least ~~one layer~~ two layers from the first group of layers on the at least one layer from the second group of layers wherein the stacking of the first, second and third groups of layers cause the vias in the second group of layers to contact the conductive lines in the first and third groups of layers to form an inductor buried within a dielectric substrate with each turn of the inductor comprising one conductive line from each layer of the first and third groups of layers and the conductive vias from the second group of layers and wherein, with respect to each turn of the inductor, the one conductive lines from each layer of the first group of layers are parallel and in juxtaposition to form a top of the each turn of the inductor and the one conductive lines from each layer of the

third group of layers are parallel and in juxtaposition to form a bottom of the each turn of the inductor..

15. (Original) The method of claim 14 wherein the respective layers are greensheets and the inductor and dielectric substrate are unsintered and further comprising the step of: g) sintering the unsintered dielectric substrate having an unsintered inductor buried therein to form a dielectric substrate having a multiturn inductor buried therein.

Claim 16 Canceled.

17. (Original) The method of claim 14 wherein there are a plurality of layers from the second group of layers.

18. (Previously presented) The method of claim 14 wherein the vias in the second group of layers contact the conductive lines in the first and third groups of layers only at the ends of the conductive lines.

19. (Previously presented) The method of claim 14 wherein the vias in the second group of layers contact the conductive lines in the first and third groups of layers along the length of the conductive lines.

20. (Currently amendedl) A method of forming a dielectric substrate having a multiturn inductor, the method comprising the steps of:

a) obtaining a plurality of layers;

b) forming conductive lines on a first group of layers;

c) forming conductive vias in a second group of layers;

d) forming conductive lines on a third group of layers;

e) stacking at least one layer from the second group of layers on at least one layer from the third group of layers; and

f) stacking at least one layer from the first group of layers on the at least one layer from the second group of layers wherein the stacking of the first, second and third groups of layers cause the vias in the second group of layers to contact the conductive lines in the first and third groups of layers to form an inductor buried within a dielectric substrate. ~~The method of claim 14~~ wherein the multiturn inductor is in the form of a toroidal shape.

21. (Previously presented) The method of claim 14 wherein the conductive lines in the first and third groups of layers are planar in shape so as to comprise a flat portion having a width and a thickness less than the width, the conductive vias having a circular contact surface and the flat portion of the conductive lines in the first and third groups of layers in contact with the circular contact surface of the conductive vias.

22. (Previously presented) The method of claim 14 wherein the conductive lines in the first and third groups of layers are planar wiring lines and the conductive vias having a

circular contact surface wherein the planar wiring lines directly contact the circular contact surface of the conductive vias.

23. (Previously presented) The method of claim 14 wherein the conductive lines in the first and third groups of layers each comprise at least two parallel wiring lines of unequal length in juxtaposition.

24. (New) A method of forming a dielectric substrate having a multiturn inductor, the method comprising the steps of:

a) obtaining a plurality of layers;

b) forming conductive lines on a first group of layers;

c) forming conductive vias in a second group of layers;

d) forming conductive lines on a third group of layers;

e) stacking a first layer from the third group of layers;

f) stacking at least one layer from the second group of layers on the one layer from the third group of layers;

g) stacking a second layer from the third group of layers;

h) stacking at least one layer from the second group of layers on the second layer from the third group of layers;

i) stacking a first layer from the first group of layers on the at least one layer from the second group of layers in h);

j) stacking at least one layer from the second group of layers on the first layer from the first group of layers;

(k) stacking a second layer from the first group of layers on the at least one layer from the second group of layers; and

(l) wherein the stacking of the first, second and third groups of layers cause the vias in the second groups of layers to contact the conductive lines in the first and third groups of layers to form an inductor buried within a dielectric substrate with each turn of the inductor comprising one conductive line from each layer of the first and third groups of layers and the conductive vias from the second group of layers and wherein, with respect to each turn of the inductor, the one conductive lines from each layer of the first group of layers are parallel and in juxtaposition to form a top of the each turn of the inductor and the one conductive lines from each layer of the third group of layers are parallel and in juxtaposition to form a bottom of the each turn of the inductor.